

National Exams - December 2003
98-Elec-B11, Electro-Optical Engineering

3 hours duration

NOTES:

1. If doubt exists as to the proper interpretation of any question, the candidate is urged to submit with the answer paper, a clear statement about any assumptions made.
2. Candidates may use one of two calculators, the Casio or Sharp approved models.
3. This is a "**Closed-Book**" examination. The candidate may have a single 8.5 inch by 11 inch sheet (both sides) of hand-written notes as an aid for the examination.
4. Any **five** questions constitute a complete paper. Only the first five questions as they appear in your answer book will be marked.
5. All questions are of equal value.
6. This examination paper has 4 pages.

Values of common constants:

$$\epsilon_0 = 8.854 \times 10^{-12} \text{ F/m}$$

$$\mu_0 = 4\pi \times 10^{-7} \text{ H/m}$$

$$c = 2.998 \times 10^8 \text{ m/s}$$

$$q = 1.602 \times 10^{-19} \text{ C}$$

$$h = 6.626 \times 10^{-34} \text{ J}\cdot\text{s}$$

$$K = 1.381 \times 10^{-23} \text{ J/}^\circ\text{K}$$

$$0^\circ\text{K} = -273^\circ\text{C}$$

$$1 \text{ \AA} = 1.0 \times 10^{-10} \text{ m}$$

$$\text{Si} \quad \epsilon_r = 11.8$$

$$\text{Si} \quad n = 3.42$$

$$\text{Si} \quad E_g = 1.11 \text{ eV}$$

$$\text{Ge} \quad \epsilon_r = 16.0$$

$$\text{Ge} \quad n = 4.01$$

$$\text{Ge} \quad E_g = 0.67 \text{ eV}$$

$$\text{GaAs} \quad \epsilon_r = 13.2$$

$$\text{GaAs} \quad n = 3.63$$

$$\text{GaAs} \quad E_g = 1.41 \text{ eV}$$

$$\text{InGaAsP} \quad n = 3.5$$

$$\text{LiNbO}_3 \quad \epsilon_r = 32$$

$$\text{LiNbO}_3 \quad n_o = 2.30$$

Useful formulas:

$$\int \frac{dx}{a^2 + x^2} = \frac{1}{a} \arctan\left(\frac{x}{a}\right)$$

$$P(n) = \frac{N^n \exp(-N)}{n!}$$

$$I_s = R_o \sqrt{P_o P_1} \cos \theta$$

$$n(E) = n_0 - \frac{1}{2} m_0^3 E$$

$$x_{1,2} = \frac{-b \pm \sqrt{b^2 - 4ac}}{2a}$$

Question 1

A multimode fiber has core diameter $100\ \mu\text{m}$, core refractive index 1.475, and a cladding refractive index of 1.455. The fiber is operated at $\lambda=850\ \text{nm}$.

- Calculate the V-number for the fiber and estimate the number of modes.
- Calculate the wavelength beyond which the fiber becomes single mode.
- Calculate the numerical aperture of the fiber and the maximum acceptance angle.
- For NRZ signaling, calculate the modal dispersion $\Delta\tau$ and hence the BL product given that the rms dispersion is $\sigma=0.29\ \Delta\tau$ in which $\Delta\tau$ is measured at FWHM.
- Explain why modal dispersion is reduced in a GRIN fiber compared with the step-index fiber.

Question 2

A Ge pn-junction photodiode has a measured responsivity shown in Figure 1. Its photosensitive area is 0.008mm^2 . It is used under reverse bias of 10V when the dark current is $0.3\ \mu\text{A}$ and the junction capacitance is 4 pF. The transit time of the photodiode is 0.5 ns.

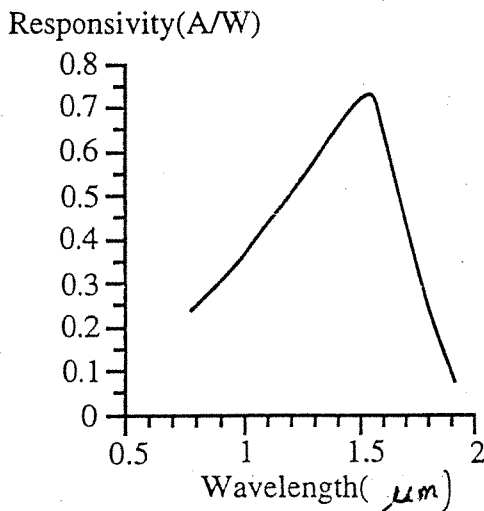


Figure 1. Responsivity of Ge photodiode.

- Calculate the quantum efficiency at 850, 1300, and 1550 nm.
- What is the intensity of light at 1550 nm that gives a photocurrent equal to the dark current?
- What would be the effect of lowering the temperature on the responsivity curve?
- Given that the dark current is in the range of microamperes, what would be the advantage in lowering the temperature?
- Suppose that the photodiode is used with a $100\ \Omega$ resistance to sample the photocurrent. What is the bandwidth for detection?
- Explain the difference between the photovoltaic mode and the photoconductor mode of operation of a detector diode. What are the advantages and disadvantages of each?

Question 3

- (a) Explain why population inversion is essential to the operation of a laser diode.
- (b) Show that the ratio between the output power P_1 from mirror 1 with a reflectance R_1 and the output power P_2 from mirror 2 with reflectance R_2 in a Fabry-Perot cavity of a laser operating in steady-state is given by

$$\frac{P_2}{P_1} = \frac{1 - R_2}{1 - R_1} \sqrt{\frac{R_1}{R_2}}$$

- (c) Consider a semiconductor Fabry-Perot optical cavity of length $200 \mu\text{m}$ with end mirrors that have reflectance 80%. The refractive index of the semiconductor is 3.7. Calculate the cavity mode nearest to the free space wavelength of 1300nm .
- (d) For the same cavity, calculate the frequency separation of the modes, the finesse of the cavity, and the spectral width of each mode in GHz and in nm.

Question 4

A PCM-ASK system having a data transmission rate 250 Mb/s at a wavelength $1.3 \mu\text{m}$ must have a signal-to noise ratio of 13 dB in the detected signal for a $\text{BER} = 10^{-9}$. The quantum efficiency of the PIN photodiode is 0.65. Neglect amplifier noise. The operating temperature is 27°C . Assume the signal threshold is set half-way between the two signal levels for a detected "1" and "0". Calculate the sensitivity of the system for the following three different detection schemes.

- (a) An ideal shot-noise limited direct detector.
- (b) Direct detection, including thermal noise from a load resistor of $1 \text{ K } \Omega$.
- (c) A homodyne detector, with local oscillator power of 0 dBm and phase error of 20 degrees.

Question 5

- (a) Explain how photoconductive gain occurs in a photoconductor.
- (b) Consider a GaAs photoconductor in which carriers are generated at a rate of $G_L = 10^{20} \text{ cm}^{-3} \text{ s}^{-1}$. The device area is $10 \mu\text{m} \times 10 \mu\text{m}$ and the length is $10 \mu\text{m}$. The material parameters of the device are:

Background doping, $N_d = 10^{16} \text{ cm}^{-3}$; $N_a = 0$

Applied voltage, $V_{app} = 1.0 \text{ Volt}$

Electron velocity at the applied field, $v_e = 6 \times 10^6 \text{ cm/s}$

Hole velocity at the applied field, $v_h = 10^6 \text{ cm/s}$

Electron lifetime, $t_e = 10^{-7} \text{ s}$

Hole lifetime, $t_h = 10^{-8} \text{ s}$

Calculate,

- (i) the excess carrier concentration
- (ii) the steady state photocurrent
- (iii) the photoconductive gain.
- (c) Explain why the gain bandwidth product is almost constant for a photoconductor.

Question 6

A digital fiber optical communication system using NRZ (non return-to-zero) light pulses at a wavelength of $1.55 \mu\text{m}$, is going to be used to send signals with a bit rate between 100 Mbits/s and 10 Gbits/s at a maximum BER (bit-error-rate) value of 10^{-12} . The maximum allowed pulse broadening is half a bit period and the system security margin should be 5 dB. The following components are available to build the system.

Laser:

InGaAsP DFB laser with an output power of 10 mW and spectral width of 1 \AA .
Coupling loss from laser to fiber is 5 dB.

Fiber:

Single-mode silica glass fiber with dispersion $25\text{ps}/(\text{km}\cdot\text{nm})$ and loss $0.2\text{dB}/\text{km}$

Detector:

InGaAsP - pin diode,
Coupling loss from fiber to detector is 3 dB.
Needs a minimum of 500 photons/bit to achieve a BER value of 10^{-12} .

- Make a log (y =fiber length) - log(x = bit rate) sketch of the maximum allowed fiber length due to the attenuation limit and due to the dispersion limit for bit rates at 10Mb/s, 100 Mb/s, 1Gb/s and 10 Gb/s.
- For what fiber length (and at what bit rate), is the system limit due to attenuation and dispersion the same?
- What is the theoretical limit for the minimum number of photons/bit that is needed to get a BER value of 10^{-12} ?

Question 7

A longitudinal electro-optic Pockel cell modulator of LiNbO_3 is designed for modulation of the red laser line (635 nm) from a HeNe laser. The crystal has cylindrical geometry with a diameter of 20 mm and a length of 30 mm. The RC limited bandwidth of the modulator is 100 MHz, where R is the load resistance and C is the (parallel plate) capacitance of the crystal.

- Make a sketch of the Pockel-cell modulator together with the necessary external components that are needed. Briefly explain how the modulation is achieved.
 - Calculate the minimum "half-wave" voltage needed for the modulator.
 - What power does the sinusoidal signal generator need to operate the modulator at 100% modulation index?
 - What is the main advantage of a transverse electro-optic Pockel-cell modulator?
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